

## SINGLE INVERTER GATE

### Description

The 74LVCE1G04 is a single inverter gate with a standard totem pole output. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

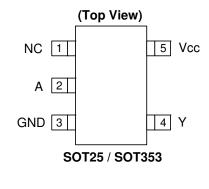
The gate performs the positive Boolean function:

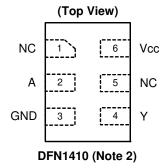
$$Y = \overline{A}$$

#### Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Input accepts up to 5.5V
- ESD Protection Tested per JESD 22
  Exceeds 200-V Machine Model (A115-A)
  Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353, and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

# Pin Assignments





#### Applications

- Voltage Level Shifting
- General Purpose Logic
- Wide array of products such as.
  - o PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders
- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.
  - 2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

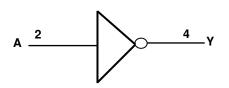


## SINGLE INVERTER GATE

## **Pin Descriptions**

Pin Name	Description			
NC	No connection			
А	Data Input			
GND	Ground			
Y	Data Output			
Vcc	Supply Voltage			

## Logic Diagram



## **Function Table**

Inputs	Output
Α	Y
Н	L
L	Н



## SINGLE INVERTER GATE

## Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
Ι <sub>ΟΚ</sub>	Output Clamp Current	-50	mA
Ι <sub>Ο</sub>	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



# SINGLE INVERTER GATE

# **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit	
N/		Operating	1.4	5.5	V	
$V_{CC}$	Operating Voltage	Data retention only	1.2		V	
		V <sub>CC</sub> = 1.4 V to 1.95 V	0.65 X V <sub>CC</sub>			
N/		$V_{\rm CC}$ = 2.3 V to 2.7 V	1.7		v	
V <sub>IH</sub>	High-level Input Voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V	
		$V_{\rm CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	0.7 X V <sub>CC</sub>			
		V <sub>CC</sub> = 1.4 V to 1.95 V		0.35 X V <sub>CC</sub>		
V		$V_{\rm CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$		0.7	v	
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V	
		$V_{\rm CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$		0.3 X V <sub>CC</sub>		
VI	Input Voltage	•	0	5.5	V	
Vo	Output Voltage		0	V <sub>CC</sub>	V	
		Vcc=1.4 V		-3		
		V <sub>CC</sub> = 1.65 V		-4		
		$V_{\rm CC} = 2.3  \rm V$		-8		
I <sub>OH</sub>	High-level output current			-16	mA	
		$V_{CC} = 3 V$		-24		
		$V_{CC} = 4.5 V$		-32		
		Vcc=1.4 V		3		
		V <sub>CC</sub> = 1.65 V		4		
		$V_{\rm CC} = 2.3  \rm V$		8	mA	
I <sub>OL</sub>	Low-level output current	<u> </u>		16		
		$V_{CC} = 3 V$		24		
		$V_{\rm CC} = 4.5 \text{ V}$		32		
		$V_{CC} = 1.4$ to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{\rm CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	rate	$V_{CC} = 5 V \pm 0.5 V$		5		
T <sub>A</sub>	Operating free-air temperature		-40	85	°C	

Note: 4. Unused inputs should be held at Vcc or Ground.



## SINGLE INVERTER GATE

## **Electrical Characteristics** (All typical values are at Vcc = 3.3V, T<sub>A</sub> = $25^{\circ}$ C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
		I <sub>OH</sub> = -100μA	1.4 V to 5.5V	$V_{CC} - 0.1$			
		I <sub>OH</sub> = -3mA	1.4 V	1.05			
		I <sub>OH</sub> = -4mA	1.65 V	1.2			
V <sub>OH</sub>	High Level Output Voltage	$I_{OH} = -8mA$	2.3V	1.9			V
	Vollage	I <sub>OH</sub> = -16mA	3 V	2.4			
		I <sub>OH</sub> = -24mA	3 V	2.3			
		I <sub>OH</sub> = -32mA	4.5 V	3.8			
		$I_{OL} = 100 \mu A$	1.4 V to 5.5V			0.1	
		$I_{OL} = 3mA$	1.4V			.4	
		$I_{OL} = 4mA$	1.65 V			0.45	V
$V_{OL}$	High-level Input Voltage	$I_{OL} = 8mA$	2.3V			0.3	
		$I_{OL} = 16 \text{mA}$	3 V			0.4	
		$I_{OL} = 24mA$	5 V			0.55	
		$I_{OL} = 32mA$	4.5			0.55	
I <sub>I</sub>	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA
I <sub>OFF</sub>	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5 V$	0			± 10	μA
I <sub>CC</sub>	Supply Current	$V_1 = 5.5V \text{ of } GND$ $I_0=0$	1.4 V to 5.5V			10	μA
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF
		SOT25	(Note 5)		204		
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W
		DFN1410	(Note 5)		430		1
		SOT25	(Note 5)		52		
$\theta_{\rm JC}$	Thermal Resistance	SOT353	(Note 5)		143		°C/W
	Junction-to-Case	DFN1410	(Note 5)		190		1

Over recommended free-air temperature range (unless otherwise noted)

Note: 5. Test condition for SOT25, SOT353, and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## SINGLE INVERTER GATE

## **Switching Characteristics**

Parameter From		ТО	Vcc = ± 0			1.8 V .15V		2.5 V 0.2V		: 3.3 V ).3V		= 5 V ).5V	Unit
(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Мах			
t <sub>pd</sub>	А	Y	2	6.4	1.4	4.4	0.8	3.3	0.5	2.7	0.5	2.7	ns

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From	то	Vcc = ± 0			: 1.8 V .15V		: 2.5 V ).2V	Vcc = ± 0	: 3.3 V ).3V		= 5 V ).5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	•
t <sub>pd</sub>	А	Y	3	7.5	2.1	5.2	1.1	4.1	0.8	3.4	0.9	3.3	ns

### **Operating Characteristics**

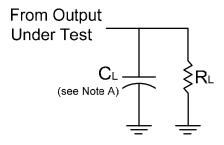
 $T_A = 25 \ ^{o}C$ 

Р	arameter	Test	Vcc = 1.5 V	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
-	Conditions		ТҮР	ТҮР	ТҮР	ТҮР	TYP	•
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	16	16	18	18	20	pF

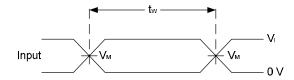


## SINGLE INVERTER GATE

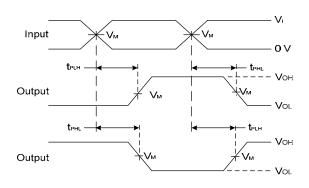
### **Parameter Measurement Information**



Vcc	Vcc		V	0.	RL	
VCC	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	ոլ	
1.5V±0.1V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
1.8V±0.15V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1MΩ	



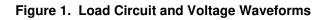
Voltage Waveform Pulse Duration



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance.

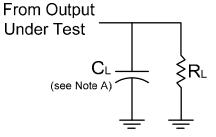
- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



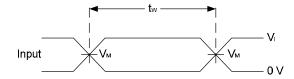


## SINGLE INVERTER GATE

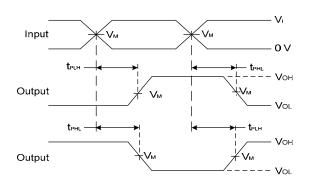
### Parameter Measurement Information (Continued)



Vcc	Vcc		V <sub>M</sub>	CL	RL	
	VI	t <sub>r</sub> /t <sub>f</sub>	- 101	<u>-</u> L		
1.5V±0.1V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ	
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω	
3.3V±0.3V	ЗV	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω	



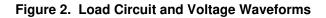
Voltage Waveform Pulse Duration



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance.

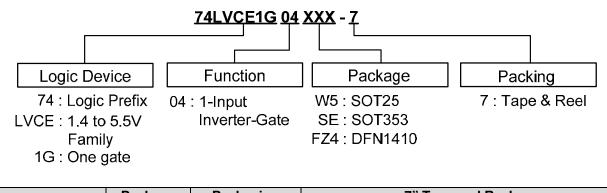
- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$





# SINGLE INVERTER GATE

### **Ordering Information**



	Device	Package	Packaging	7" Tape a	nd Reel
	Device	Code	(Note 5)	Quantity	Part Number Suffix
<b>Pb</b> ,	74LVCE1G04W5-7	W6	SOT25	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G04SE-7	SE	SOT353	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G04FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

Note:

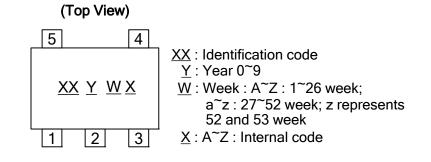
6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



## SINGLE INVERTER GATE

### **Marking Information**

#### (1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVCE1G04W5	SOT25	PU
74LVCE1G04SE	SOT353	PV

#### (2) DFN1410H4-6

#### (Top View)



- $\frac{XX}{Y} : Identification Code$  $\frac{Y}{W} : Year : 0~9$  $\frac{W}{W} : Week : A~Z : 1~26 week;$ 
  - a~z : 27~52 week; z represents 52 and 53 week X : A~Z : Internal code
  - X : A~Z : Internal code

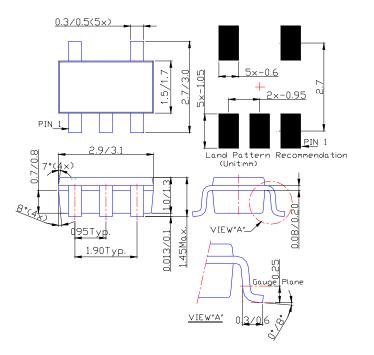
Part Number	Package	Identification Code
74LVCE1G04FZ4	DFN1410	PU



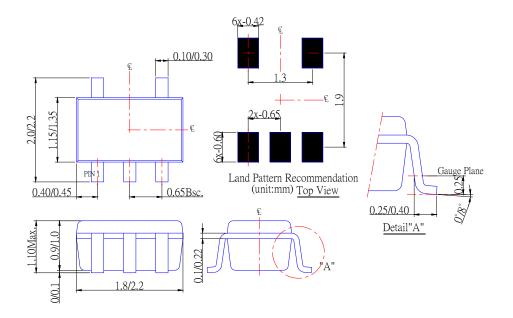
## SINGLE INVERTER GATE

### Package Outline Dimensions (All Dimensions in mm)

#### (1) Package Type: SOT25



#### (2) Package Type: SOT353



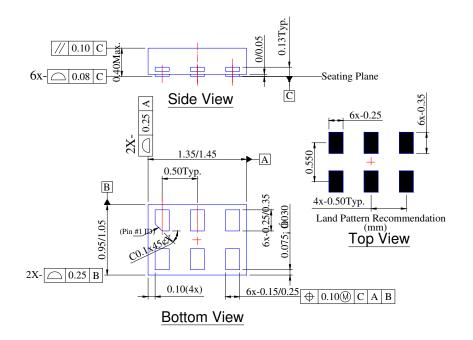
74LVCE1G04 Document number: DS32212 Rev. 2 - 2



## SINGLE INVERTER GATE

### Package Outline Dimensions (All Dimensions in mm)

### (3) Package Type: DFN1410

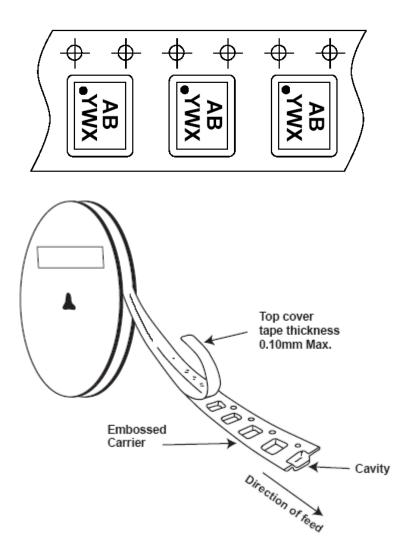




# SINGLE INVERTER GATE

### Taping Orientation (Note 7)

#### For DFN1410







### SINGLE INVERTER GATE



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